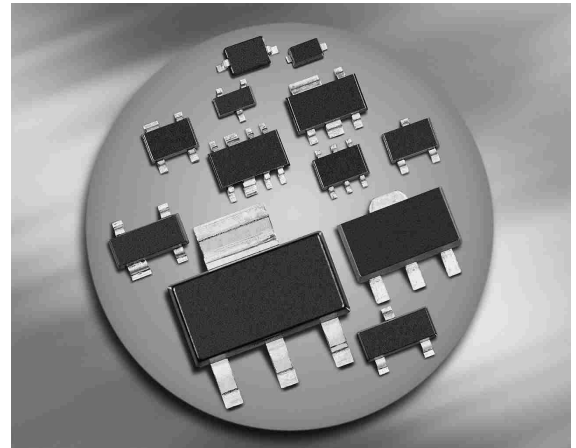
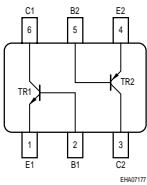


NPN/PNP Silicon AF Transistor Arrays

- For AF input stage and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Two (galvanic) internal isolated NPN/PNP transistor in one package
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



BC846PN
BC846UPN
BC847PN



Type	Marking	Pin Configuration						Package
BC846PN	1Os	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BC846UPN	1Os	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SC74
BC847PN	1Ps	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage BC846PN/UPN BC847PN	V_{CEO}	65 45	V
Collector-emitter voltage BC846PN/UPN BC847PN	V_{CES}	80 50	
Collector-base voltage BC846PN/UPN BC847PN	V_{CBO}	80 50	
Emitter-base voltage	V_{EBO}	6	
Collector current	I_C	100	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	200	
Total power dissipation- $T_S \leq 115^\circ\text{C}$, BC846PN, BC847PN $T_S \leq 118^\circ\text{C}$, BC846UPN	P_{tot}	250 250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾ BC846PN, BC847PN BC846UPN	R_{thJS}	≤ 140 ≤ 130	K/W

¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 10\text{ mA}$, $I_B = 0$, BC846PN/UPN $I_C = 10\text{ mA}$, $I_B = 0$, BC847PN	$V_{(BR)CEO}$	65 45	- -	- -	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$, BC846PN/UPN $I_C = 10\text{ }\mu\text{A}$, $I_E = 0$, BC847PN	$V_{(BR)CBO}$	80 50	- -	- -	
Collector-emitter breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $V_{BE} = 0$, BC846PN/UPN $I_C = 10\text{ }\mu\text{A}$, $V_{BE} = 0$, BC847PN	$V_{(BR)CES}$	80 50	- -	- -	
Emitter-base breakdown voltage $I_E = 1\text{ }\mu\text{A}$, $I_C = 0$	$V_{(BR)EBO}$	6	-	-	
Collector-base cutoff current $V_{CB} = 50\text{ V}$, $I_E = 0$ $V_{CB} = 30\text{ V}$, $I_E = 0$, $T_A = 150^\circ\text{C}$	I_{CBO}	- -	- -	0.015 5	μA
DC current gain- $I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$	h_{FE}	- 200	250 290	- 450	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{CEsat}	- -	90 200	300 650	mV
Base emitter saturation voltage ⁻¹⁾ $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{BEsat}	- -	700 900	- -	
Base-emitter voltage ⁻¹⁾ $I_C = 2\text{ mA}$, $V_{CE} = 5\text{ V}$ $I_C = 10\text{ mA}$, $V_{CE} = 5\text{ V}$	$V_{BE(ON)}$	580 -	660 -	750 820	

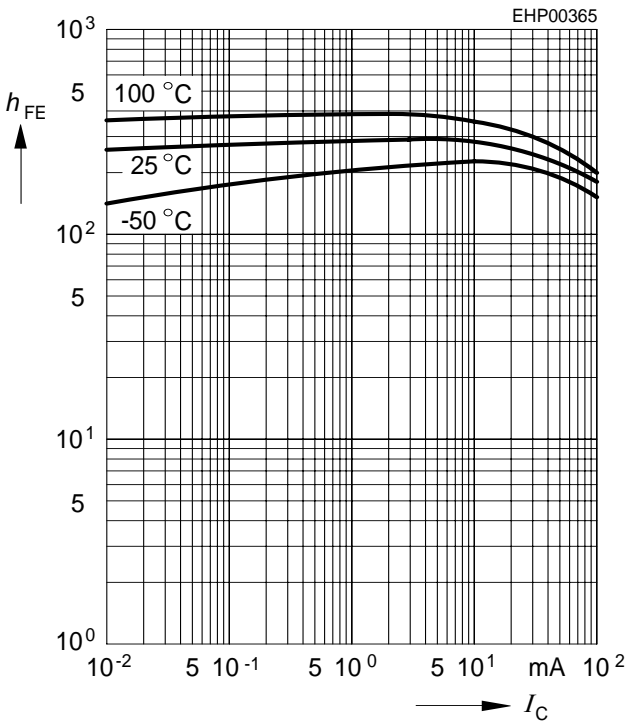
¹⁾Pulse test: $t = 300\mu\text{s}$, $D = 2\%$

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 10\text{ mA}, V_{CE} = 5\text{ V}, f = 100\text{ MHz}$	f_T	-	250	-	MHz
Collector-base capacitance $V_{CB} = 10\text{ V}, f = 1\text{ MHz}$	C_{cb}	-	1.5	-	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}, f = 1\text{ MHz}$	C_{eb}	-	8	-	
Short-circuit input impedance $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}$	h_{11e}	-	4.5	-	k Ω
Open-circuit reverse voltage transf. ratio $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}$	h_{12e}	-	2	-	10^{-4}
Short-circuit forward current transf. ratio $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}$	h_{21e}	-	330	-	-
Open-circuit output admittance $I_C = 2\text{ mA}, V_{CE} = 5\text{ V}, f = 1\text{ kHz}$	h_{22e}	-	30	-	μS

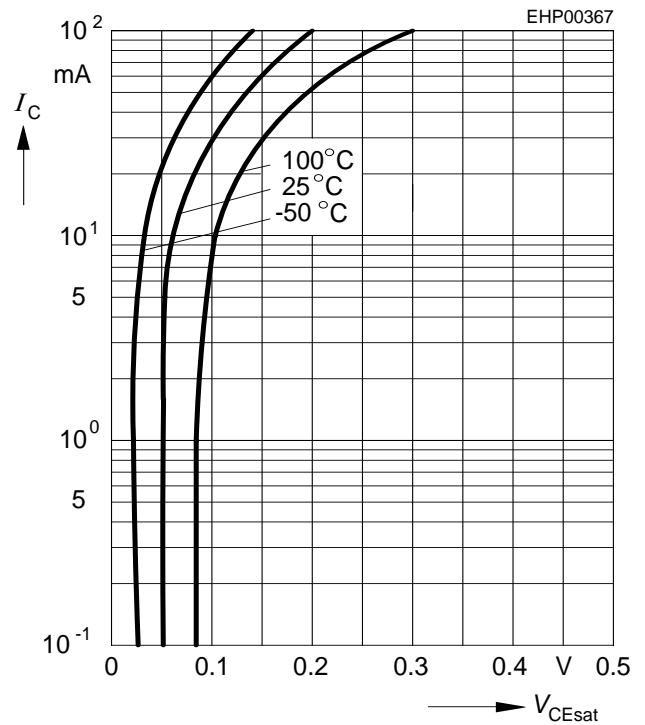
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5\text{ V}$



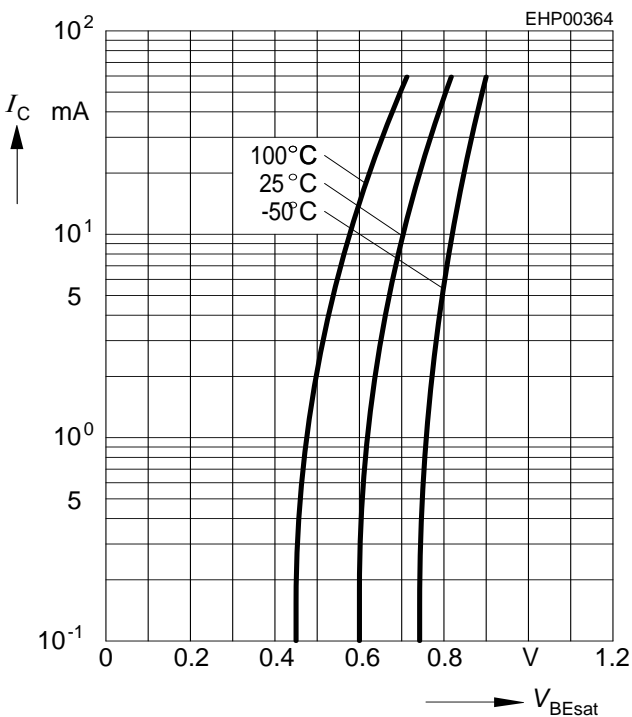
Collector-emitter saturation voltage

$I_C = f(V_{CEsat}), h_{FE} = 20$



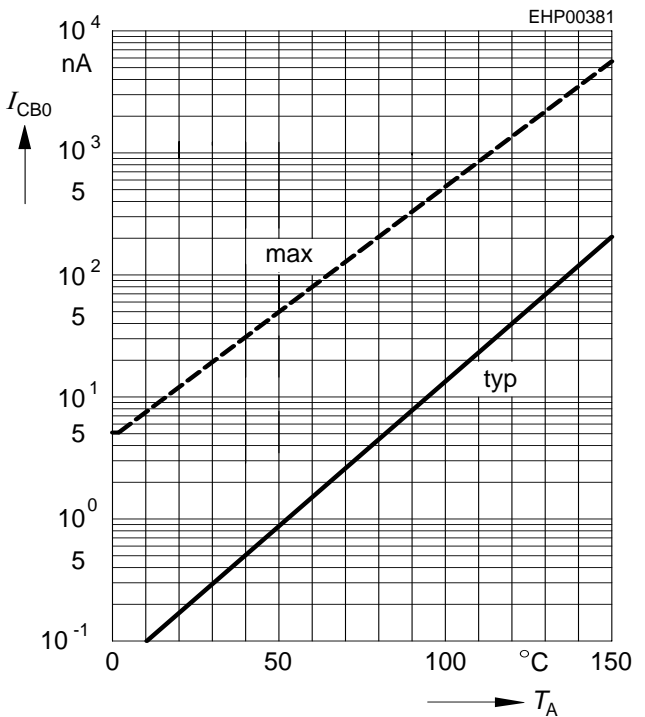
Base-emitter saturation voltage

$I_C = f(V_{BEsat}), h_{FE} = 20$



Collector cutoff current $I_{CBO} = f(T_A)$

$V_{CBO} = 30\text{ V}$



Transition frequency $f_T = f(I_C)$

$V_{CE} = 5\text{ V}, f = 100\text{ MHz}$



Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$



Total power dissipation $P_{tot} = f(T_S)$

BC846PN, BC847PN



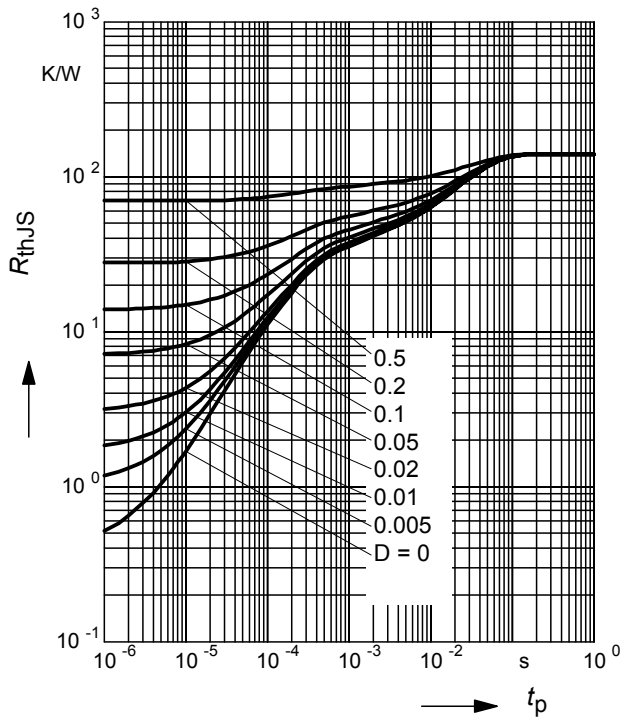
Total power dissipation $P_{tot} = f(T_S)$

BC846UPN



Permissible Pulse Load $R_{thJS} = f(t_p)$

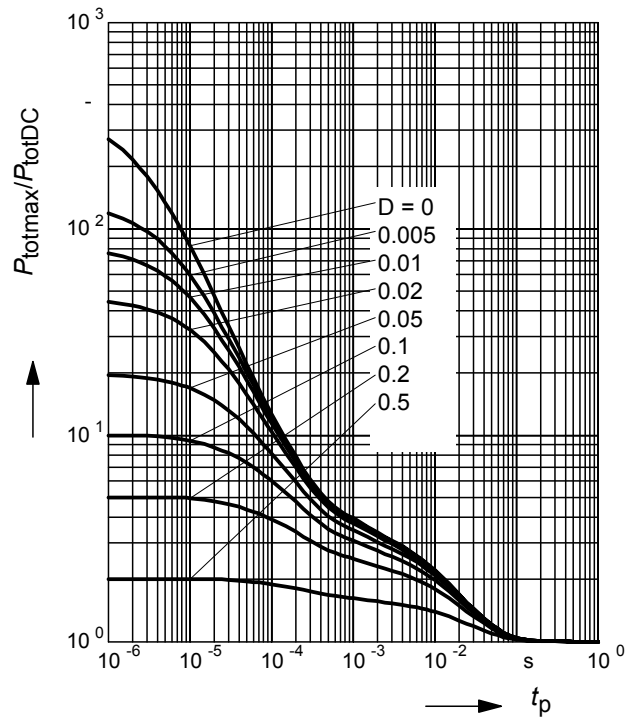
BC846PN, BC847PN



Permissible Pulse Load

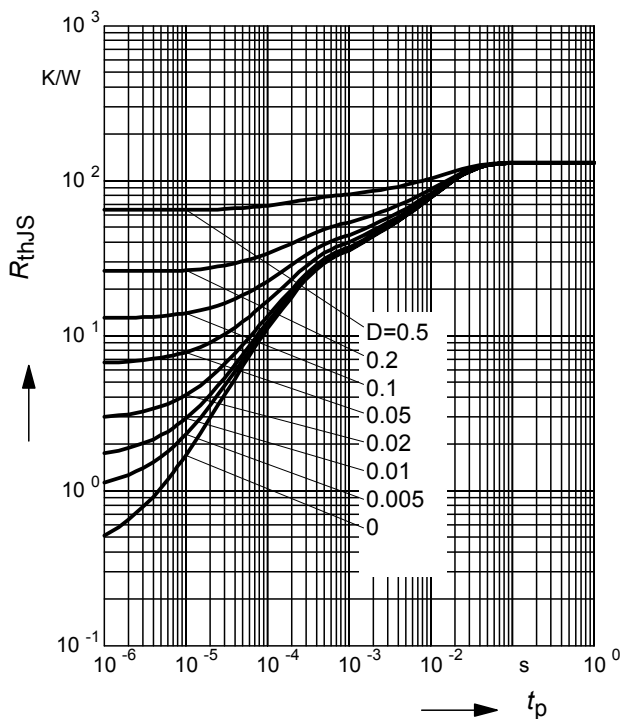
$P_{totmax}/P_{totDC} = f(t_p)$

BC846PN, BC847PN



Permissible Puls Load $R_{thJS} = f(t_p)$

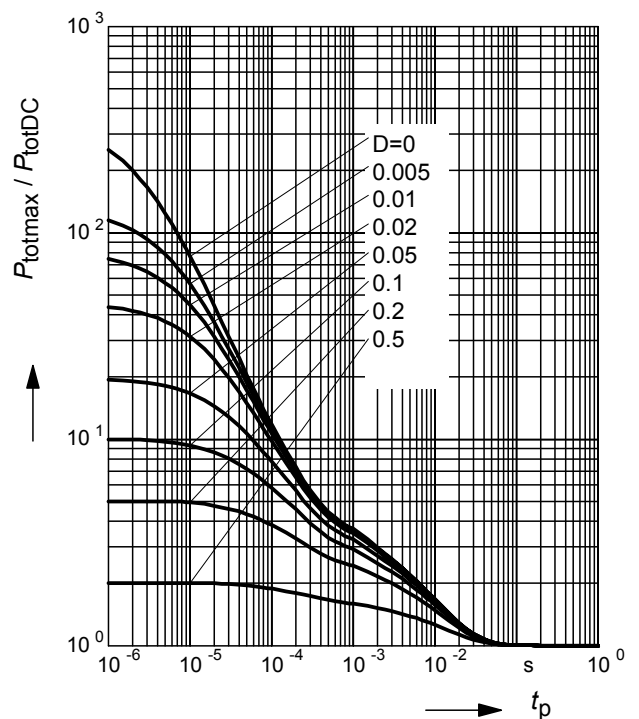
BC846UPN



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

BC846UPN



Package Outline



Foot Print



Marking Layout (Example)

Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



Package Outline



Foot Print



Marking Layout (Example)

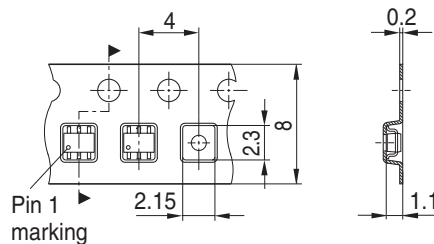
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
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For symmetric types no defined Pin 1 orientation in reel.



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